

Fabrication of (001)-oriented monoclinic WO<sub>3</sub> films on FTO substrates†Cite this: *Nanoscale*, 2013, 5, 5279

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(001)-oriented monoclinic nanorod and microplate WO<sub>3</sub> films are fabricated on commercial FTO-coated glass substrates by a rubbing seed layer and a spin-coating seed layer assisted by hydrothermal reactions. The nanorod film obtained by the rubbing seed layer assisted by hydrothermal reactions is more regular and perpendicular to the substrate.

Tungsten trioxide (WO<sub>3</sub>), an n-type semiconductor with a smaller band gap of *ca.* 2.8 eV than that of TiO<sub>2</sub> ( $E_g = 3.2$  eV), is one of the most well-known photocatalysts for water splitting under visible light irradiation.<sup>1</sup> The hole mobility and diffusion length of WO<sub>3</sub> are 10 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup> and 0.15 μm, respectively, much better than those of α-Fe<sub>2</sub>O<sub>3</sub> (10<sup>-2</sup> to 10<sup>-1</sup> cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup> and 2–20 nm).<sup>2</sup> In addition, WO<sub>3</sub> possesses high resistance against photocorrosion and good chemical stability in an acidic environment (pH < 4) under solar illumination. Depending on the temperature and pressure, the bulk WO<sub>3</sub> crystal phase can be classified into five forms:<sup>3,4</sup> tetragonal (α-WO<sub>3</sub>), orthorhombic (β-WO<sub>3</sub>), monoclinic I (γ-WO<sub>3</sub>), triclinic (δ-WO<sub>3</sub>) and monoclinic II (ε-WO<sub>3</sub>). The monoclinic I (γ-WO<sub>3</sub>) is the most stable phase in bulk WO<sub>3</sub> at room temperature, which can be described as a distorted 2 × 2 × 2 superstructure of the normal cubic ReO<sub>3</sub>-type unit cell, by tilting the WO<sub>6</sub> octahedra and displacing the central W atom.<sup>4</sup> In the crystal structure of γ-monoclinic WO<sub>3</sub>, the bond lengths are nearly symmetric along the [100] direction, but long–short alternating along both [010] and [001] directions.<sup>5</sup>

The photocatalytic reactivity of a semiconductor photocatalyst is affected by its electronic and surface atomic structures, which sensitively depend on the crystal facet with

different orientations. Li *et al.* reported that the (001) surface of γ-monoclinic WO<sub>3</sub> has the lowest surface energy compared with other facets.<sup>6</sup> Recently, Valdés and Kroes showed that the photo-oxidation of water on the γ-monoclinic WO<sub>3</sub> (200) surface requires an overpotential of 1.04 V, 1.10 V for the (020) surface and 1.05 V for the (002) surface by using DFT calculations.<sup>7</sup> Jin *et al.*<sup>8</sup> have performed DFT calculations on the structural and electronic properties of the (001) facet of γ-monoclinic WO<sub>3</sub>. Most recently, Xie *et al.*<sup>9</sup> reported a quasi-cubic-like monoclinic WO<sub>3</sub> crystal with a nearly equal percentage of {002}, {200} and {020} facets, which show a much higher photocatalytic oxidation activity of H<sub>2</sub>O for O<sub>2</sub> evolution; a {002} dominant rectangular sheet-like WO<sub>3</sub> with an elevated conduction band minimum of 0.3 eV can reduce CO<sub>2</sub> to CH<sub>4</sub> under light illumination. In addition, they also gave a surface energy order of {002} (1.56 J m<sup>-2</sup>) > {020} (1.54 J m<sup>-2</sup>) > {200} (1.43 J m<sup>-2</sup>), which indicates that {200} is the most stable and {002} is the most unstable. The active sites at the catalyst surface and the underlying reaction mechanisms in photocatalytic processes of WO<sub>3</sub> are still not clear and are attracting many researchers' interest.

Considering the practical application, WO<sub>3</sub> thin films are more popular than powder types since film types can be used for electrochromic devices,<sup>10–12</sup> gas sensors<sup>13,14</sup> and photochemical electrodes.<sup>15,16</sup> WO<sub>3</sub> films can be prepared by various methods such as sputtering,<sup>17–19</sup> evaporation,<sup>18</sup> chemical vapor deposition (CVD),<sup>20</sup> pulsed laser deposition (PLD),<sup>21</sup> molecular beam epitaxy (MBE),<sup>22</sup> sol–gel,<sup>23</sup> electrochemical deposition,<sup>16</sup> hydrothermal reaction<sup>10–12,15,24</sup> and so on. However, the properties of the films are significantly affected by the films' crystallinity and texture which are dependent on various process parameters and the type of substrate used.<sup>19</sup> In addition, as mentioned above, since the properties of WO<sub>3</sub> crystals sensitively depend on the dominant crystal facets, it is important to achieve the epitaxial growth of WO<sub>3</sub> films. Many studies on the investigation of the epitaxial growth of WO<sub>3</sub> films on sapphire,<sup>17–20</sup> MgO<sup>17</sup> and SrTiO<sub>3</sub> (ref. 19) substrates by sputtering or CVD methods have been reported. However, these fabrication techniques are

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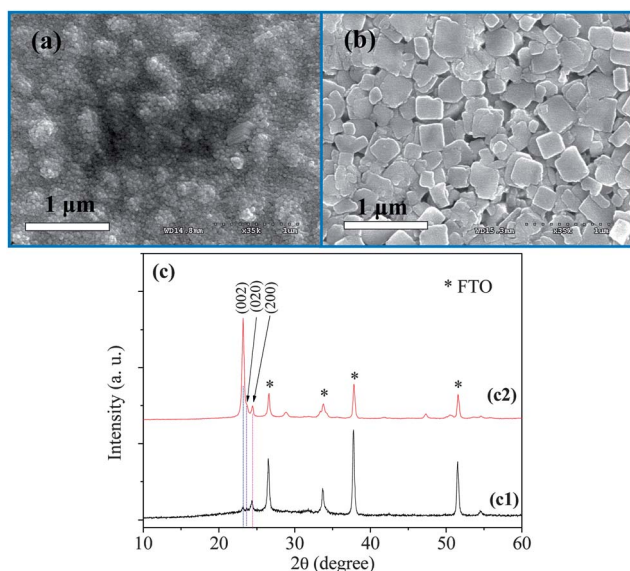
expensive and require extreme experimental conditions such as high temperature and high vacuum; in addition, these substrates are electrical insulators although their crystal lattices highly match with  $\text{WO}_3$ . For using in solar conversion devices such as solar cells and solar water splitting, it is very important to achieve the epitaxial growth of  $\text{WO}_3$  films on transparent conductive substrates such as indium-doped tin oxide (ITO) and fluorine-doped tin oxide (FTO) coated glasses. The comparison between ITO and FTO is that the electrical resistance of ITO will be increased tremendously while the resistance of FTO is stable at high temperature annealing.<sup>25</sup>

Particularly, Sun's<sup>10–12,15</sup> and Grimes's<sup>24</sup> groups have performed many studies on fabrication of  $\text{WO}_3$  films on FTO coated glass by a hydrothermal method; however, these films are not one facet oriented. It is challenging and promising to produce (001) facet oriented monoclinic tungsten trioxide films. Herein, (001)-oriented monoclinic nanorod and microplate  $\text{WO}_3$  films are fabricated on commercial FTO substrates by a rubbing seed layer (RSL) or spin-coating seed layer (SSL) assisted by hydrothermal reactions using different capping agents. The photocurrents of nanorod and microplate films are comparatively discussed.

Fig. 1 shows the SEM images and XRD patterns of seed layers made by spin-coating and rubbing methods after calcination treatment. The reflection peaks of the produced  $\text{WO}_3$  films completely fit with monoclinic phase  $\text{WO}_3$  (JCPDS no. 43-1035). The differences between these two methods are as follows: (i) the sizes of  $\text{WO}_3$  seeds on FTO are different. The seeds made by the spin-coating method are very small (<50 nm) and the layer composed of them is attached to FTO very well. In contrast, the size of  $\text{WO}_3$  seeds made by the rubbing method is about 300 nm, which is completely dependent on the size of the rubbing crystals as shown in Fig. S1(a).† The size limitation for direct attachment is from about 0.5  $\mu\text{m}$  to 3  $\mu\text{m}$  with respect to rate, degree of close packing, uniform orientation of the assembled microcrystals,

substrate area, and ecological considerations.<sup>26</sup> Therefore, compared to the other accurate technologies such as PLD, MBE and so on, the rubbing method is not good at making ultra thin monolayer films using the particles with the thickness lower than 200 nm. However, the rubbing method can fabricate films with one-axis orientation without necessarily considering the crystal lattice matching between rubbing materials and substrates. Herein, the rubbing layer is not perfect since the assembled  $\text{WO}_3$  nanoplates are not uniform enough and the size of which is around 300 nm, less than the lower limit size of 500 nm. (ii) The crystallinity and dominant crystal facet of  $\text{WO}_3$  seed layers are different. The spin-coating seed layer has low crystallinity and the dominant crystal facet cannot be controlled artificially as shown in Fig. 1(c)c1. For the rubbing seed layer, the crystallinity is very high and the dominant crystal facet is (002), which can be attributed to the intrinsic nature of a single crystalline  $\text{WO}_3$  nanoplate with dominant facet (002). Some other crystal facets are also rarely exposed, such as (020) and (200). The peak intensity ratios of (002) to (020) and (200) are  $I_{(002)}/I_{(020)} = 6.08$  and  $I_{(002)}/I_{(200)} = 6.88$  as shown in Table 1. Compared with those of  $\text{WO}_3$  powder samples for rubbing, the ratios of dominant crystal facet (002) to (020) and (200) increase about 5 times as shown in Table 1. Therefore, we believe that if the homogeneous micro-sized single crystalline  $\text{WO}_3$  plates can be made, only the (002)-oriented  $\text{WO}_3$  film can be prepared on substrates such as glass, FTO or ITO coated glass by the rubbing method.

Fig. 2(a) and (b) show the top-view and cross-sectional SEM images of the  $\text{WO}_3$  film obtained by RSL assisted by a hydrothermal method using citric acid as a capping agent. The vertically oriented  $\text{WO}_3$  nanorod array film with a thickness of ca. 900 nm was obtained and the transverses of nanorods were square or rectangle. It indicated that  $\text{WO}_3$  nanorods grew along the [001] orientation. With the same natural conclusion, the  $\text{WO}_3$  crystal would preferably grow along the [001] orientation because the (001) facet is more active than the other facets.<sup>27</sup> The XRD pattern in Fig. 2(c) also completely fits with monoclinic phase tungsten trioxide (JCPDS no. 43-1035). The  $I_{(002)}/I_{(020)}$  is 16.73 and the  $I_{(002)}/I_{(200)}$  is 25.73. They are much higher than  $I_{(002)}/I_{(020)}$  and  $I_{(002)}/I_{(200)}$  of  $\text{WO}_3$  powder and the rubbing seed layer. The (002) facets in all nanorod crystals obtained by RSL assisted by hydrothermal reactions are the most exposed facets under X-ray irradiation. To study the photoelectrochemical property of this film,

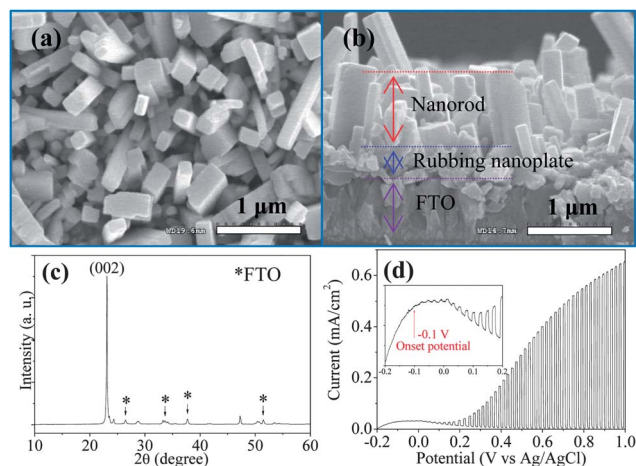


**Fig. 1** SEM images and XRD patterns of the seed layers made by (a and c1) spin-coating and (b and c2) rubbing methods after calcination in air at 500 °C for 2 h.

**Table 1** XRD peak intensity ratios of (002) to (020) and (200) of different samples. RSL: rubbing seed layer; SSL: spin-coating seed layer

Samples	$I_{(002)}/I_{(020)}$	$I_{(002)}/I_{(200)}$
$\text{WO}_3$ powder (see Fig. S1)	1.33	1.27
RSL	6.08	6.88
RSL after hydrothermal growth	16.73	25.73
SSL	1.17	0.71
SSL after hydrothermal growth <sup>a</sup>	9.60	5.38
SSL assisted by the hydrothermal method at different pHs		
pH 1.9	1.86	4.25
pH 2.3	0.83	1.58
pH 2.5	2.21	3.05

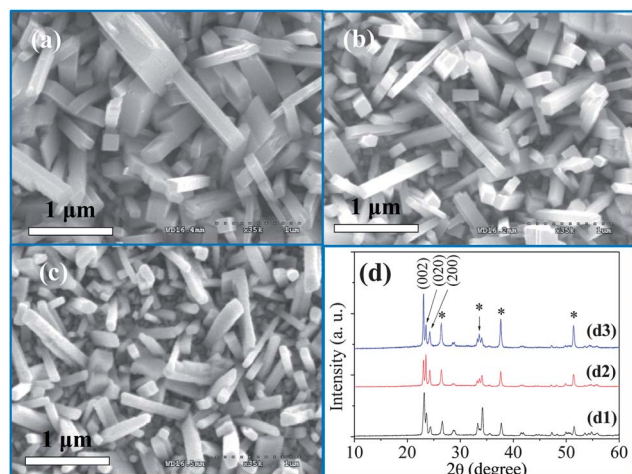
<sup>a</sup> The crystal phase mixed with a little orthorhombic  $\text{WO}_3 \cdot 0.33\text{H}_2\text{O}$ .



**Fig. 2** (a) Top-view and (b) cross-sectional SEM images and (c) XRD pattern of the as-synthesized  $\text{WO}_3$  film by the rubbing seed layer assisted by a hydrothermal method at  $180^\circ\text{C}$  for 24 h using 0.1 mol citric acid as a capping agent. (d) Photocurrent of the film after calcination in air at  $500^\circ\text{C}$  for 2 h. The inset is a magnified curve from  $-0.2$  to  $0.2$  V.

the current–potential property was checked in 0.5 M  $\text{Na}_2\text{SO}_4$  solution (pH 6.3) under chopped (1 Hz: light on and off) 1 sun light illumination. The photocurrent onset potential is approximately  $-0.1$  V vs. Ag/AgCl and the photocurrent is *ca.*  $0.65$  mA  $\text{cm}^{-2}$  at  $1.0$  V vs. Ag/AgCl.

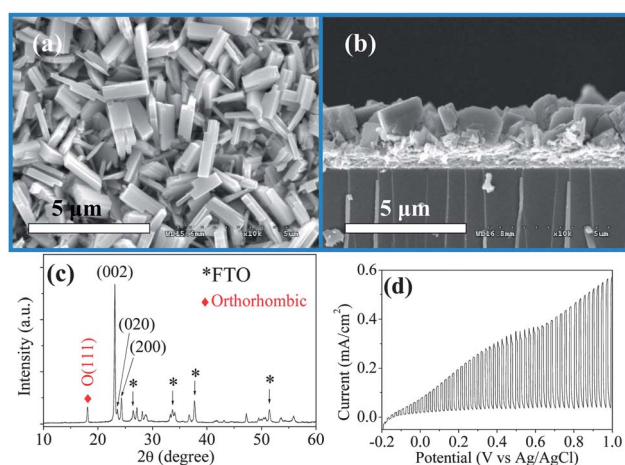
Considering that the  $\text{WO}_3$  product is sensitive to the pH of reaction solution, the morphology study of the resultant product dependent on the pH of solution was carried out at different pHs of the reaction solution as shown in Fig. 3. Herein, we used SSL assisted by a hydrothermal method since the RSL was not perfectly uniform as mentioned previously. All of the rod arrays obtained at different pHs were not completely vertical. At initial pH 1.9, the cuboid rods were very sharp and had very clear surfaces. However, some incomplete plate-like



**Fig. 3** SEM images and XRD patterns of  $\text{WO}_3$  films synthesized by the spin-coating seed layer assisted by a hydrothermal method at  $180^\circ\text{C}$  for 12 h using 0.1 mol citric acid as a capping agent at different pH values. (a and d1) Initial pH 1.9, (b and d2) pH 2.3, and (c and d3) pH 2.5 (Low magnification images are shown in Fig. S2†).

particles existed in the film. As the pH was increased to 2.3, the cuboid nanorods became homogeneous; the most transverses of nanorods were square. When pH was 2.5, the surfaces of rods became rough and were not perfectly cuboid any more. One possible reason is that the surface of  $\text{WO}_3$  can be dissolved at relatively high pH in the hydrothermal reaction. Another reason is that the pH affected the concentration of the real functional group – carboxyl group  $[-\text{COO}^-]$  of the capping agent (citric acid) in the reaction solution; as the pH is increased, the  $[-\text{COO}^-]$  increases and gives excessive capping actions. The  $I_{(200)}/I_{(020)}$  and  $I_{(002)}/I_{(200)}$  of nanorod films, obtained by SSL assisted by a hydrothermal reaction at different pH values, showed a slight increase of the crystal facet orientations to the  $\text{WO}_3$  nanoplate powder sample as shown in Table 1.

For investigating the effect of various capping agents, oxalic acid was used as a capping agent in SSL assisted by a hydrothermal reaction. The micro-sized  $\text{WO}_3$  plate film with a thickness of *ca.*  $2$   $\mu\text{m}$  was obtained as shown in Fig. 4(a) and (b). The corresponding XRD pattern as shown in Fig. 4(c) indicates that the as-obtained plate films are composed of two kinds of crystal phases: primary monoclinic  $\text{WO}_3$  and minor orthorhombic  $\text{WO}_3 \cdot 0.33\text{H}_2\text{O}$  (JCPDS no. 72-0199). This film, also regarded as monoclinic  $\text{WO}_3$  as explained in Fig. S3,† exhibits a similar phenomenon that the intensity of the (002) facet reflection peak is the biggest;  $I_{(002)}/I_{(020)}$  is 9.60 and  $I_{(002)}/I_{(200)}$  is 5.38 as shown in Table 1. It indicates that the microplates preferably grow along the same (001) direction. After ignoring the FTO peaks, orthorhombic phase peaks and most exposed (002), (020) and (200) peaks, there are still some little peaks in the pattern which means the microplate film has some irregular plate particles not vertically growing on the substrate.<sup>28,29</sup> In contrast, all the peaks except the (002) peak as shown in Fig. 2(c) almost disappeared which indicates that the nanorod film is more regular and perpendicular to the FTO substrate. Although only a few groups have synthesized tungsten trioxide nanorod films on FTO substrates,<sup>24,30–32</sup> the XRD patterns of their films actually show many high intensity peaks. To the best of our knowledge, this is



**Fig. 4** (a) Top-view and (b) cross-sectional SEM images and (c) XRD pattern of the  $\text{WO}_3$  film synthesized by the spin-coating seed layer assisted by a hydrothermal method at  $180^\circ\text{C}$  for 24 h using 0.1 mol oxalic acid as the capping agent. (d) Photocurrent of the film after calcination in air at  $500^\circ\text{C}$  for 2 h.

the first time that the vertical growth of tungsten trioxide nanorod films has been proven using XRD patterns. The HRTEM image of WO<sub>3</sub> micro-sized plates after calcination in air at 500 °C for 2 h is shown in Fig. S4(a).† The clear lattice structure and SAED pattern show that the plates are single crystalline. Their crystal lattice distances of *ca.* 0.38 nm and *ca.* 0.36 nm correspond to the *d*-spacing of the (002) and (200) planes, respectively. Fig. S4(b)† shows 10 CV scanning curves of the WO<sub>3</sub> microplate film without calcination treatment. The curves are smooth and show nearly no obvious change after 10 cycles of scanning. This indicates that the as-obtained monoclinic WO<sub>3</sub> film is very stable.<sup>10,11</sup> The general photoelectrochemical property of the WO<sub>3</sub> microplate film electrode was checked under chopped (1 Hz) 1 sun light. The photocurrent onset potential of the microplate film is around -0.2 V *vs.* Ag/AgCl, which is more negative than that of the nanorod film. The photocurrent is *ca.* 0.57 mA cm<sup>-2</sup> at 1.0 V *vs.* Ag/AgCl.

In this work, the high crystalline thermally stable monoclinic WO<sub>3</sub> films with nanorod and microplate morphologies have been synthesized by using different capping agents. The nanorod film growing on the rubbing nanoplate seed layer with high crystallinity shows high orientation along the (001) growth direction. Citric acid can be used as a capping agent for nanorod growth and the morphologies of products are sensitive to the pHs of reaction solution. The microplate film directly growing on the normal spin-coating seed layer is also (001) oriented. According to this work, it is possible to make perfectly (001)-oriented WO<sub>3</sub> films if the perfect rubbing seed layer can be made.

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## Notes and references

- 1 A. Kudo and Y. Miseki, *Chem. Soc. Rev.*, 2009, **38**, 253.
- 2 J. E. Yourey and B. M. Bartlett, *J. Mater. Chem.*, 2011, **21**, 7651.
- 3 X. Liu, F. Wang and Q. Wang, *Phys. Chem. Chem. Phys.*, 2012, **14**, 7894.
- 4 F. G. Wang, C. D. Valentin and G. Pacchioni, *J. Phys. Chem. C*, 2012, **116**, 10672.
- 5 R. Chatten, A. V. Chadwick, A. Rougier and P. J. D. Lindan, *J. Phys. Chem. B*, 2005, **109**, 3146.
- 6 M. Li, E. I. Altman, A. Posadas and C. H. Ahn, *Surf. Sci.*, 2003, **542**, 22.
- 7 Á. Valdés and G.-J. Kroes, *J. Chem. Phys.*, 2009, **130**, 114701.
- 8 H. Jin, J. Zhu, J. Hu, Y. Li, Y. Zhang, X. Huang, K. Ding and W. Chen, *Theor. Chem. Acc.*, 2011, **130**, 103.
- 9 Y. P. Xie, G. Liu, L. Yin and H. M. Chen, *J. Mater. Chem.*, 2012, **22**, 6746.
- 10 Z. Jiao, X. W. Sun, J. Wang, L. Ke and H. V. Demir, *J. Phys. D: Appl. Phys.*, 2010, **43**, 285501.
- 11 Z. Jiao, J. Wang, L. Ke, X. Liu, H. V. Demir, M. F. Yang and X. W. Sun, *Electrochim. Acta*, 2012, **63**, 153.
- 12 Z. Jiao, X. Wang, J. Wang, L. Ke, H. V. Demir, T. W. Koh and X. W. Sun, *Chem. Commun.*, 2012, **48**, 365.
- 13 L. J. LeGore, K. Snow, J. D. Galipeau and J. F. Vetelino, *Sens. Actuators, B*, 1996, **35**, 164.
- 14 M. D. Giulio, D. Manno, G. Micocci, A. Serra and A. Tepore, *J. Phys. D: Appl. Phys.*, 1997, **30**, 3211.
- 15 Z. Jiao, J. Wang, L. Ke, X. W. Sun and H. V. Demir, *ACS Appl. Mater. Interfaces*, 2011, **3**, 229.
- 16 J. C. Hill and K. S. Choi, *J. Phys. Chem. C*, 2012, **116**, 7612.
- 17 Y. Kobayashi, S. Terada and K. Kubota, *Thin Solid Films*, 1989, **168**, 133.
- 18 L. J. LeGore, O. D. Greenwood, J. W. Paulus, D. J. Frankel and R. J. Lad, *J. Vac. Sci. Technol., A*, 1997, **15**, 1223.
- 19 A. Garg, J. A. Leake and Z. H. Barber, *J. Phys. D: Appl. Phys.*, 2000, **33**, 1048.
- 20 P. Tagtstrom and U. Jansson, *Thin Solid Films*, 1999, **352**, 107.
- 21 M. J. Wang, G. J. Fang, L. Y. Yuan, H. H. Huang, Z. H. Sun, N. S. Liu, S. H. Xia and X. Z. Zhao, *Nanotechnology*, 2009, **20**, 185304.
- 22 S. Ling, D. Mei and M. Gutowski, *Catal. Today*, 2011, **165**, 41.
- 23 C. Santato, M. Odziemkowski, M. Ulmann and J. Augustynski, *J. Am. Chem. Soc.*, 2001, **123**, 10639.
- 24 J. Su, X. Feng, J. D. Sloppy, L. Guo and C. A. Grimes, *Nano Lett.*, 2011, **11**, 203.
- 25 T. Kawashima, H. Matsui and N. Tanabe, *Thin Solid Films*, 2003, **445**, 241.
- 26 J. S. Lee, J. H. Kim, Y. J. Lee, N. C. Jeong and K. B. Yoon, *Angew. Chem., Int. Ed.*, 2007, **46**, 3087.
- 27 J. Zhu, S. Wang, S. Xie and H. Li, *Chem. Commun.*, 2011, **47**, 4403.
- 28 H. Ishihara, G. K. Kannarpady, K. R. Khedir, J. Woo, S. Trigwell and A. S. Biris, *Phys. Chem. Chem. Phys.*, 2011, **13**, 19553.
- 29 X. Q. An, J. C. Yu, Y. Wang, Y. M. Hu, X. L. Yu and G. J. Zhang, *J. Mater. Chem.*, 2012, **22**, 8525.
- 30 J. Su, L. Guo, N. Bao and C. A. Grimes, *Nano Lett.*, 2011, **11**, 1928.
- 31 W. Smith, A. Wolcott, R. C. Fitzmorris, J. Z. Zhang and Y. Zhao, *J. Mater. Chem.*, 2011, **21**, 10792.
- 32 S. S. Kalanur, Y. J. Hwang, S. Y. Chae and O. S. Joo, *J. Mater. Chem. A*, 2013, **1**, 3479.